

Theory of Semiconductor Devices (반도체 소자 이론)

Chapter 14. Light Emitting Diodes

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✓ LIGHT EMITTING DIODE (LED)

 Basically p-n junction that are designed to produce light via a process called electroluminescence.

✓ ELECTROLUMINESCENCE

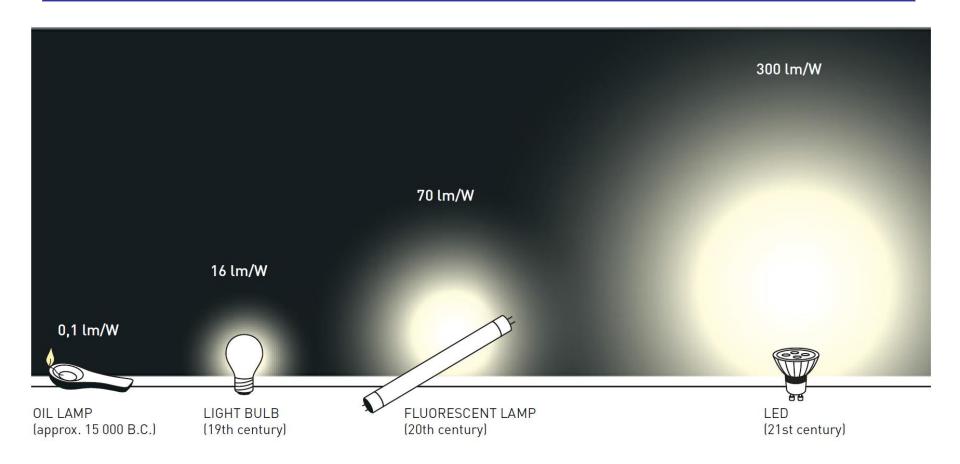
• The radiative recombination of injected minority carriers (electrons and holes) in and near the semiconductor p-n junction.

✓APPLICATION OF LED

- In & outdoor display
- Traffic signal
- Automobile indicator
- Solid state lighting
- Agriculture







- 40 % electricity savings (261 TWh) in USA in 2030 due to LEDs
- → Eliminates the 30+ (1000 MW) power plants by 2030
- → Avoids generating ~185 million tons of CO₂



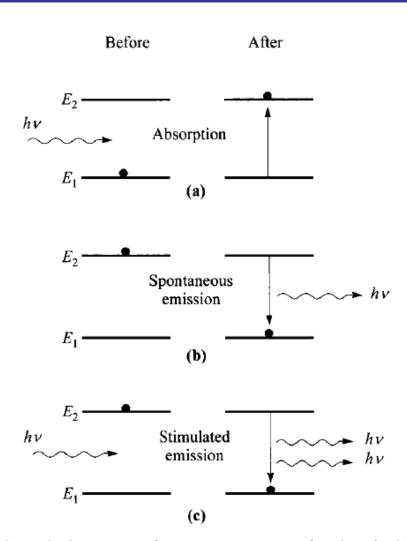


Fig. 3 The three basic optical processes between two energy levels. The black dot indicates the state of the electron. The initial state is at the left; the final state, after the process has occurred, is at the right.



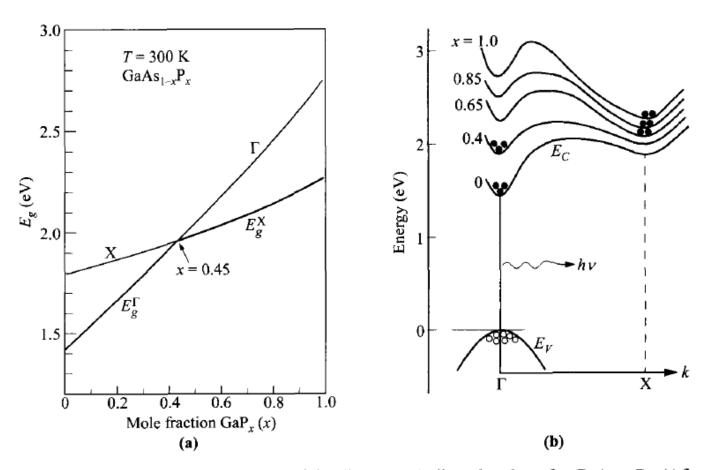
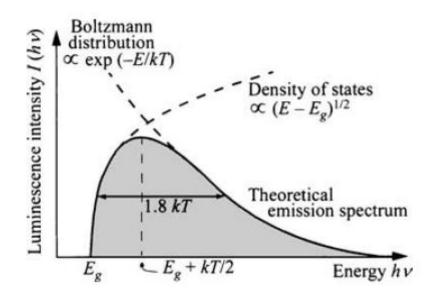
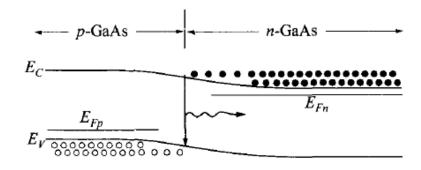
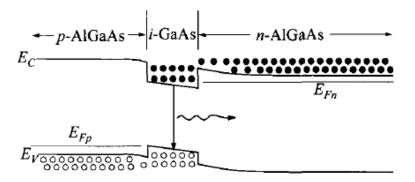


Fig. 4 (a) Composition dependence of the direct and indirect bandgap for $GaAs_{1-x}P_x$. (After Ref. 4.) (b) Energy-momentum diagram for $GaAs_{1-x}P_x$. (After Ref. 5.)

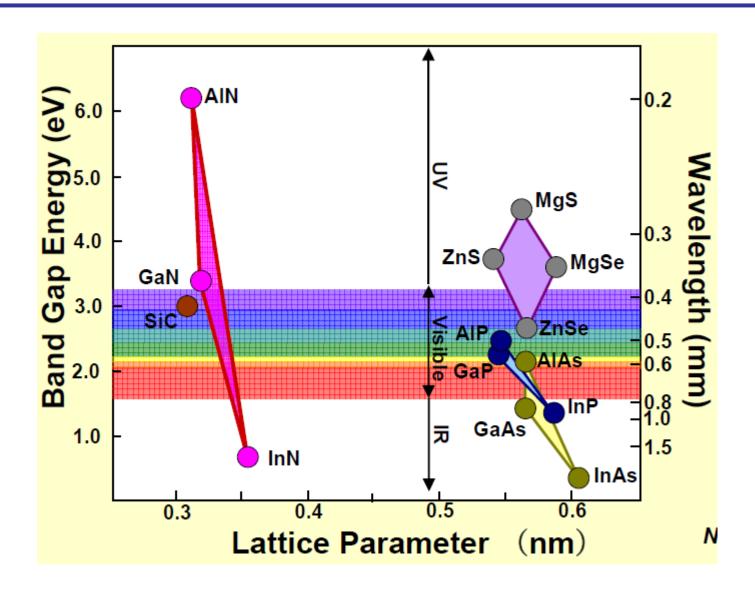




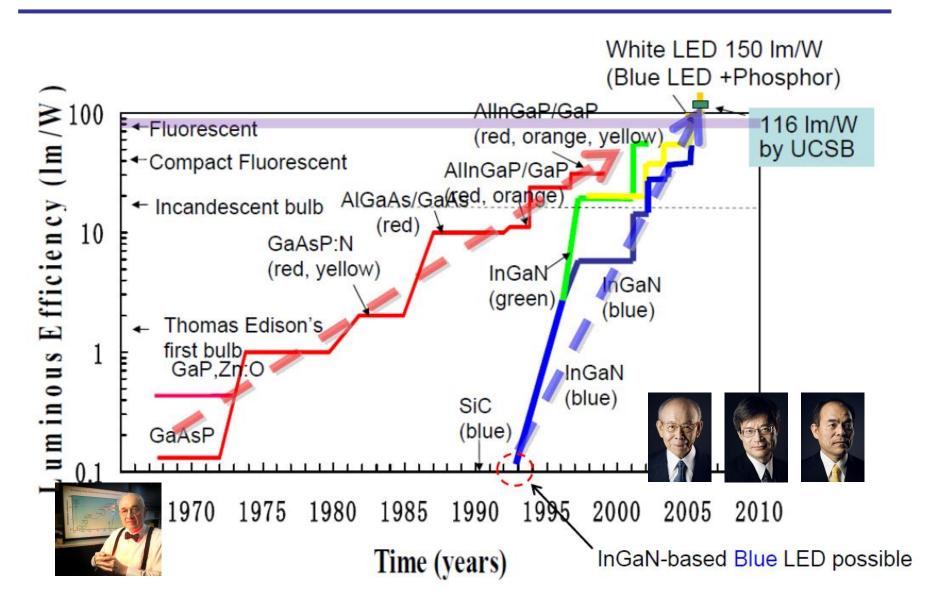














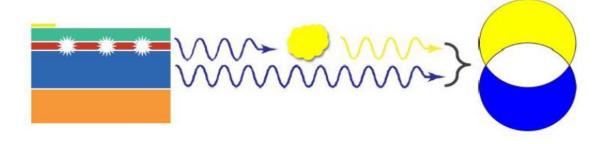
White Light: Blue + Other colors (red, yellow, green)

Other Colors: Convert Blue LED Light to Yellow using Phosphor.

Blue LED Phosphor White Light White LED

Convert: = Blue + Yellow

Blue → Yellow



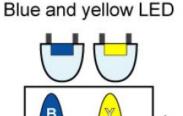


- ➤ Nichia Corp. (1996): Commercialization white LED using InGaN DH blue LED
- Nobel prize (2014) → Akasaki, Alamo, Nakamura : "for their invention of efficient blue light-emitting diodes which has enabled bright and energy-saving white light source"

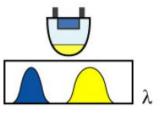




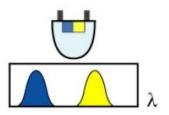
(a) Diwhite



Blue LED plus yellow phosphor

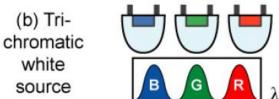


Dichromatic-LED

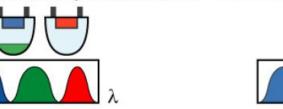


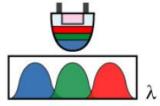
chromatic source

Blue, green, and red LED



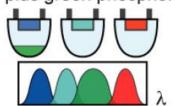
Blue and red LED plus green phosphor UV LED plus tri-phosphor



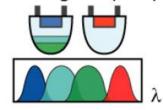




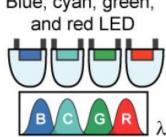
Blue, cyan, and red LED plus green phosphor



Blue and red LED plus cyan and green phosphor



(c) Tetrachromatic white source







Internal, extraction, external, and power efficiency

$$\eta_{\text{int}} = \frac{\text{\# of photons emitted from active region per second}}{\text{\# of electrons injected into LED per second}} = \frac{P_{\text{int}} / (h \nu)}{I / e}$$

$$\eta_{\text{extraction}} = \frac{\text{\# of photons emitted into free space per second}}{\text{\# of photons emitted from active region per second}}$$

$$\eta_{\text{ext}} = \frac{\text{\# of photons emitted into free space per sec.}}{\text{\# of electrons injected into LED per sec.}} = \frac{P/(hv)}{I/e} = \eta_{\text{int}} \ \eta_{\text{extraction}}$$

$$\eta_{\text{power}} = \frac{P}{IV}$$





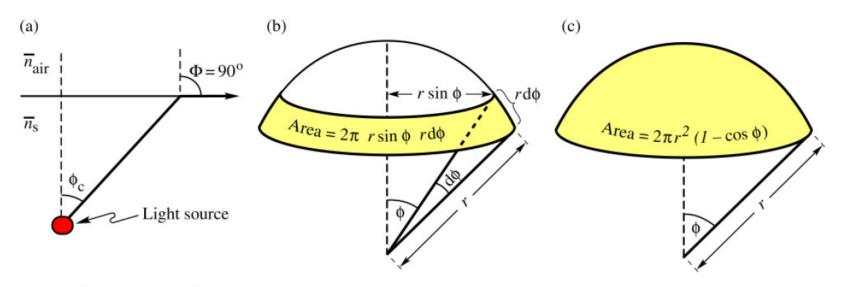


Fig. 5.3. (a) Definition of the escape cone by the critical angle ϕ_c . (b) Area element dA. (c) Area of calotte defined by radius r and angle ϕ_c .

- Total internal reflection occurs inside LED chip
- Light escape cone defined my critical angle for total internal reflection





$$\frac{P_{\text{escape}}}{P_{\text{source}}} \approx \frac{1}{2} \left[1 - \left(1 - \frac{\phi_c^2}{2} \right) \right] = \frac{1}{4} \phi_c^2$$

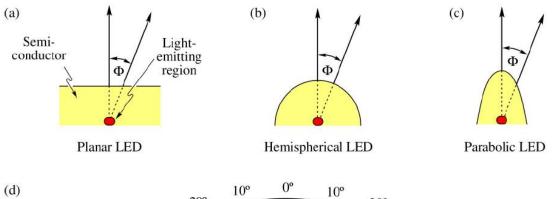
- ϕ_c = critical angle of total internal reflection
- Problem: Only small fraction of light can escape from semiconductor

$$\frac{P_{\text{escape}}}{P_{\text{source}}} = \frac{1}{4} \frac{\overline{n}_{\text{air}}^2}{\overline{n}_{\text{s}}^2}$$

 Above equation gives < 10 % extraction efficiency for typical III-V semiconductors







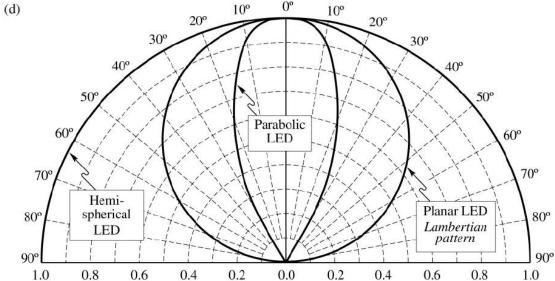


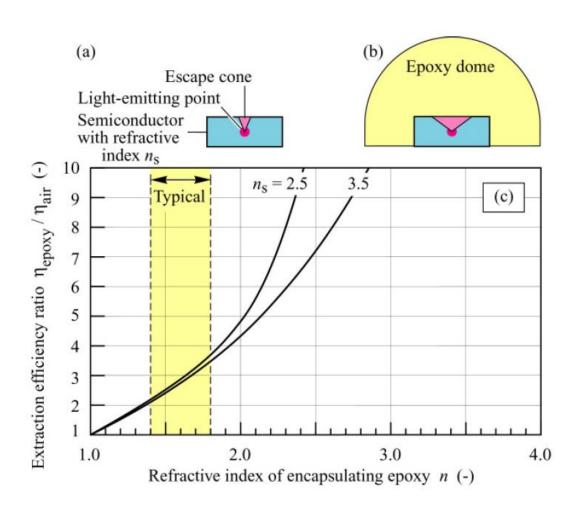
Fig. 5.5. Light-emitting diodes with (a) planar, (b) hemispherical, and (c) parabolic surfaces. (d) Far-field patterns of the different types of LEDs. At an angle of $\Phi = 60$ °, the Lambertian emission pattern decreases to 50 % of its maximum value occurring at $\Phi = 0$ °. The three emission patterns are normalized to unity intensity at $\Phi = 0$ °.

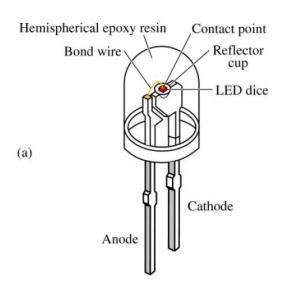
- Die shaping can change emission pattern
- "Natural" LED has a planar surface



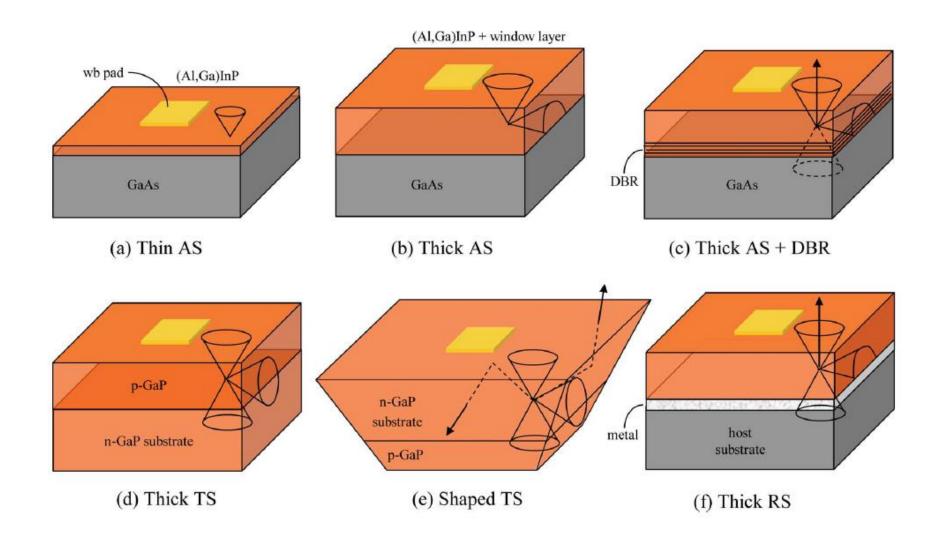




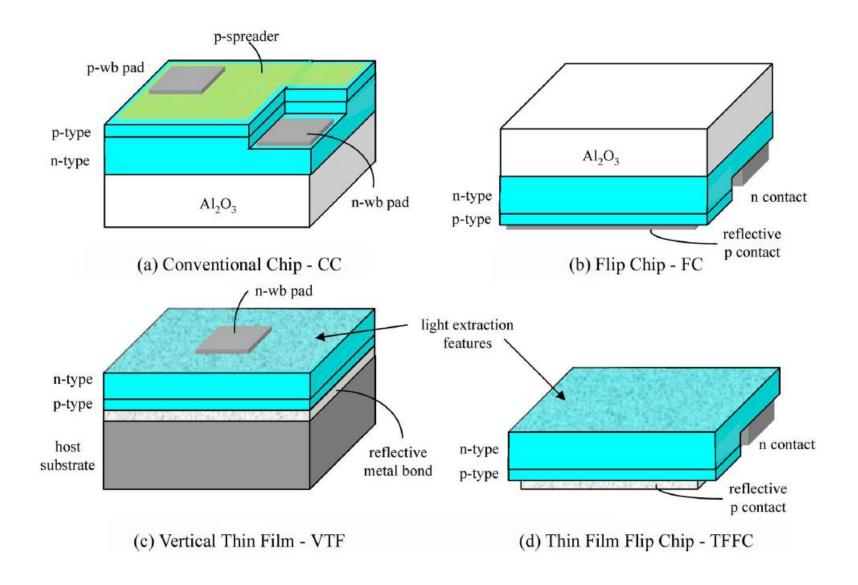














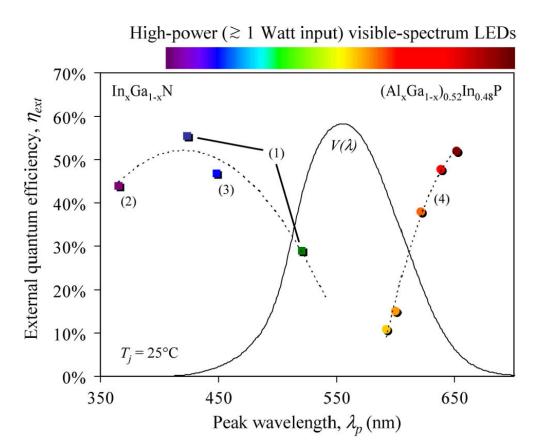
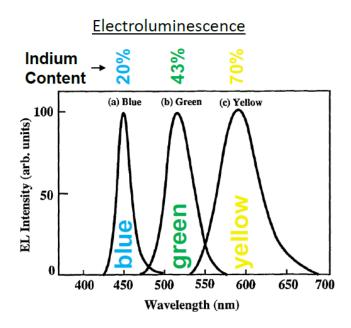


Fig. 2. State-of-art external quantum efficiencies for high-power visible-spectrum LEDs ($T_j=25~^{\circ}\text{C}$): (1) InGaN TFFC LEDs, 350 mA (this paper); (2) InGaN VTF LED, 1000 mA [42]; (3) InGaN CC LEDs employing patterned substrates [35]; and (4) Production performance, AlGaInP TIP LEDs [9], Philips Lumileds Lighting Co., 350 mA. $V(\lambda)$ is the luminous eye response curve from CIE. Dashed lines are guides to the eye.



- Highly strained InGaN layer
- High internal piezoelectric field

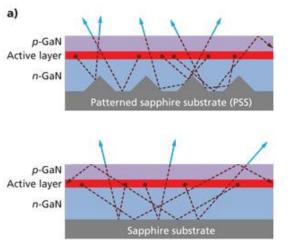


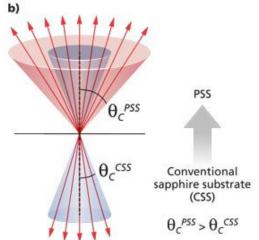


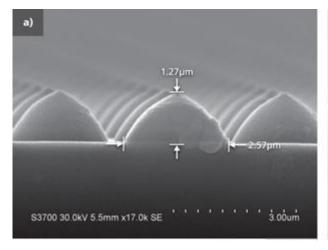
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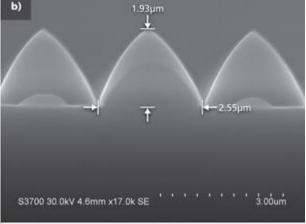
Light Emitting Diodes

Microstructures for efficient light extraction





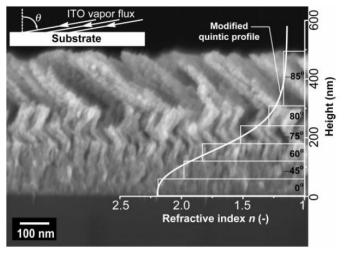


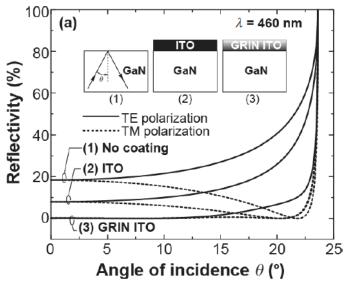


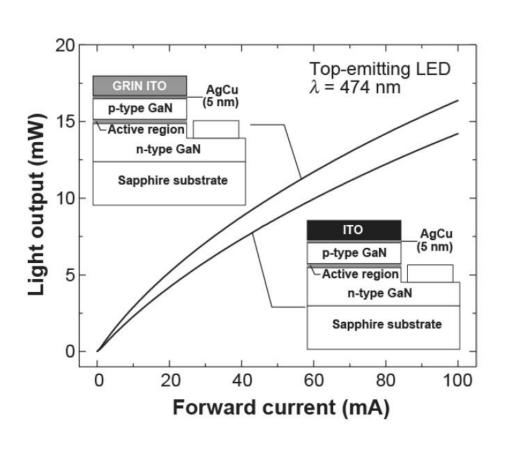
Rubicon Tech. (2014)



Nanostructures for efficient light extraction



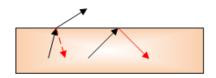




• RPI (2007)

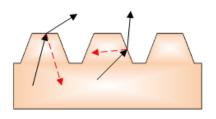


- Combination of Micro-/nano-structures
 - (i) Flat surface



Fresnel reflection (FR)
Total internal reflection
(TIR)

(ii) Micro-structure (MS)



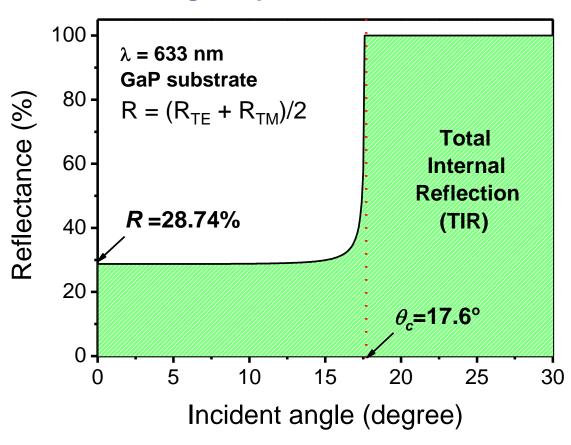
Reducing TIR

Difficult to control FR

→ Fresnel reflection

Total internal reflection

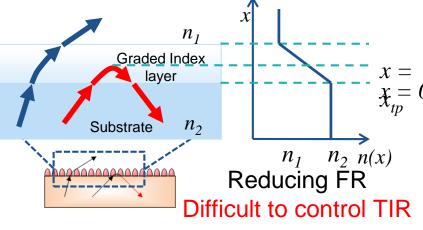
Angle dependent reflectance

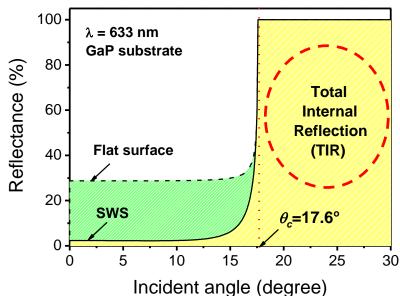


At least ~30 % reflection occurs at any incident angle!!

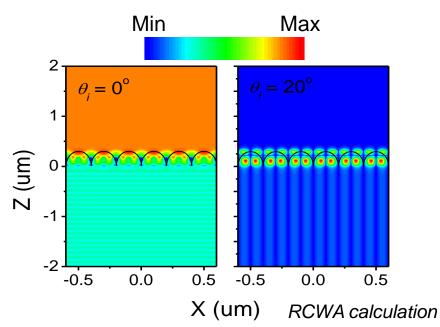


(iii) Subwavelength Structures (SWSs)





Electric field intensity distribution



The electric field cannot penetrate the SWS region at above critical angle!

LED with SWSs or graded layer

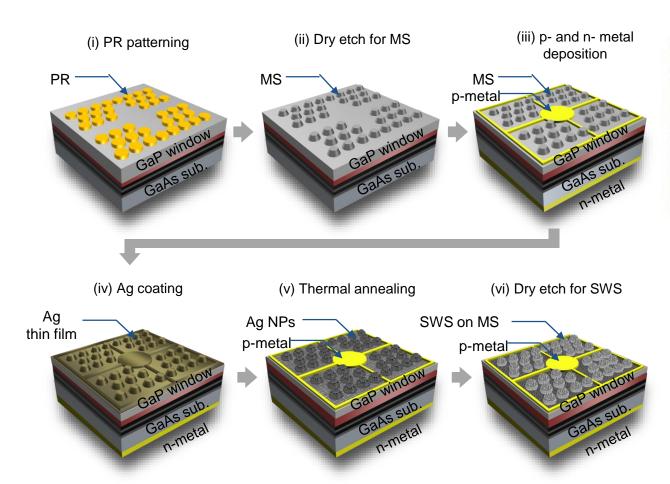
- 24.3% (J. K. Kim et al., Adv. Mater 2008)
- 26.4% (Y. M. Song et al., OE 2009) red LED
- 31% (Y.-C. Lee et al., APL 2009)
- 30.2% (Y. M. Song et al., APL 2010) blue LED



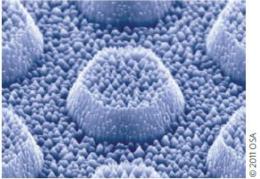


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Light Emitting Diodes



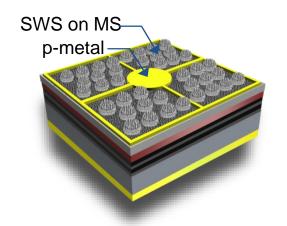
Improving LED output Opt. Express 19, A157-A165 (2011)



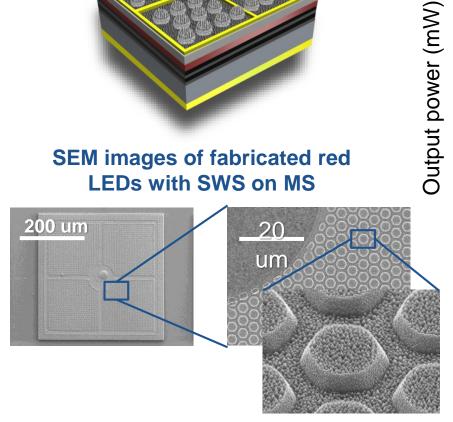
High-refractive-index LEDs often suffer from low extraction efficiency because of Fresnel reflection and total internal reflection losses. Fabricating microstructures on the surface of an LED is an efficient way of improving its efficiency, but achieving this while also reducing reflection losses has proved to be a significant challenge. Young Min Song and co-workers from South Korea have now developed a bioinspired fabrication technique that uses antireflective subwavelength structures on top of microstructures to dramatically improve the potential light output powers of an LED. They first formed hexagonally patterned microstructures with diameters of 2 µm and thicknesses of 600 nm by dry etching



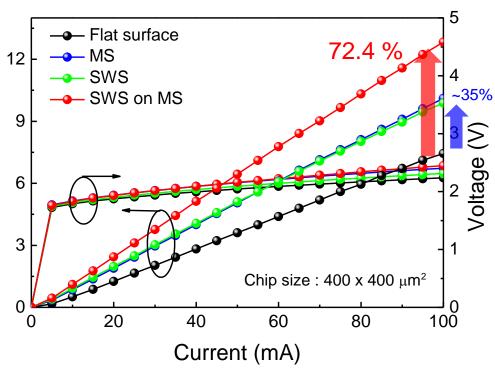
Schematic diagram for red LEDs with SWS on MS



SEM images of fabricated red **LEDs with SWS on MS**



L-I-V curve for AlGaInP LEDs with SWS on MS

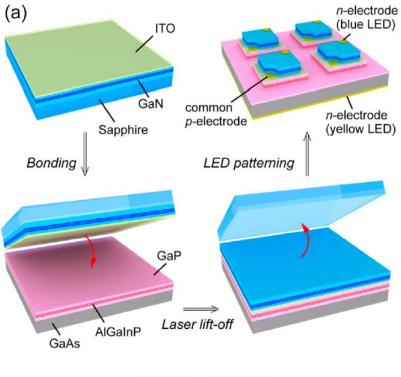


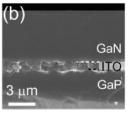
The light output power was improved by 72.4% for the LED with SWS on MS compared to the conventional LEDs

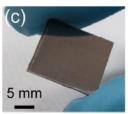


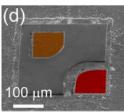


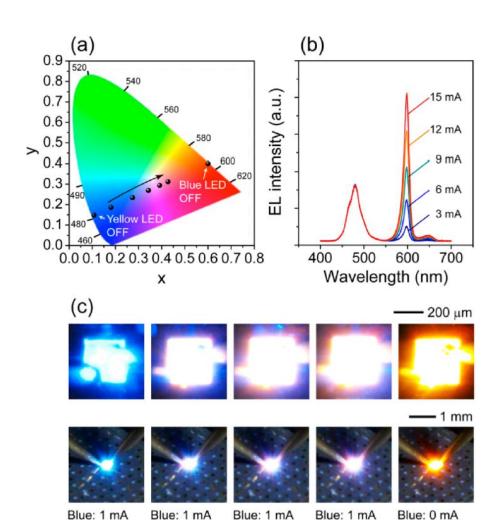
Multiple color generation











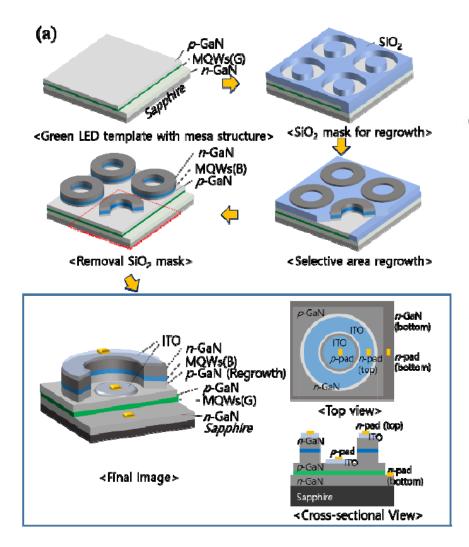
Yellow: 6 mA Yellow: 9 mA Yellow: 12 mA Yellow: 15 mA

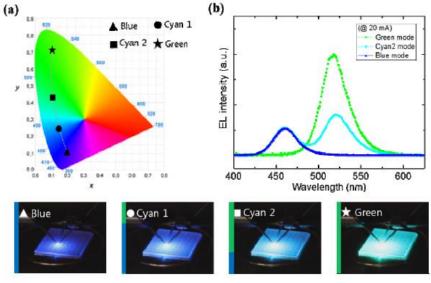
GIST, MSE (2014) 25

Yellow: 0 mA



Multiple color generation



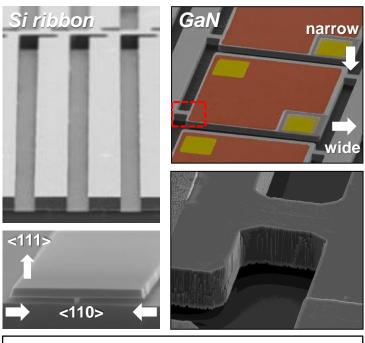


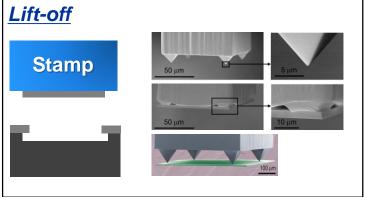
GIST, ECE (2016) 26



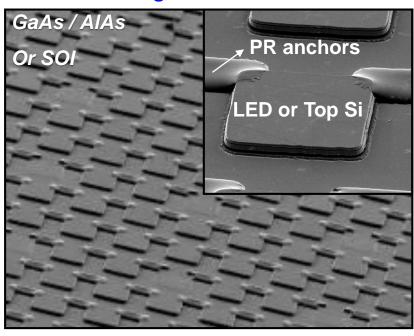
Practical approaches – Inorganic LEDs

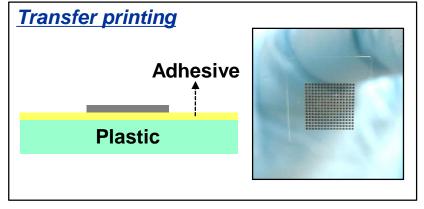
Homogeneous Anchors





Heterogeneous Anchors









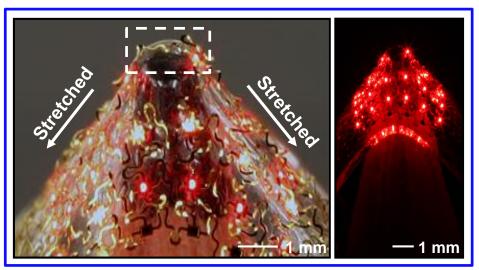
Other devices – Stretchable LEDs

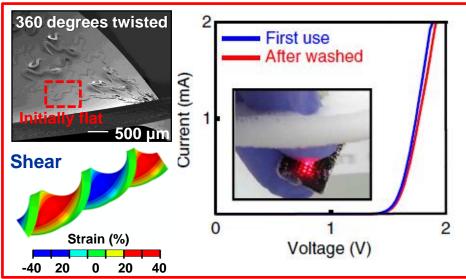
Transfer printing of ILED

(a) n-GaAs mask SiO₂ n-GaAs sacrificial layer 100 µm layers above n-GaAs (b) GaAs wafer (c) sacrificial layer removed PDMS stamp (d)

Small (2012) #42

Off-plane deformation

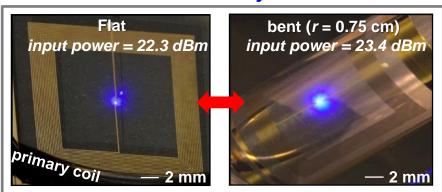




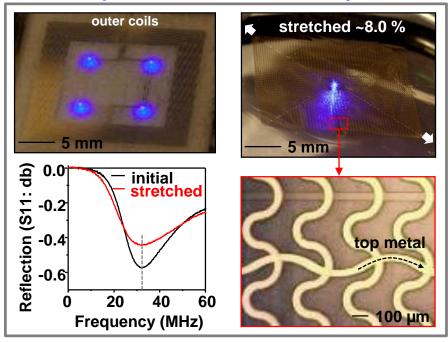


Practical approaches – Inorganic LEDs

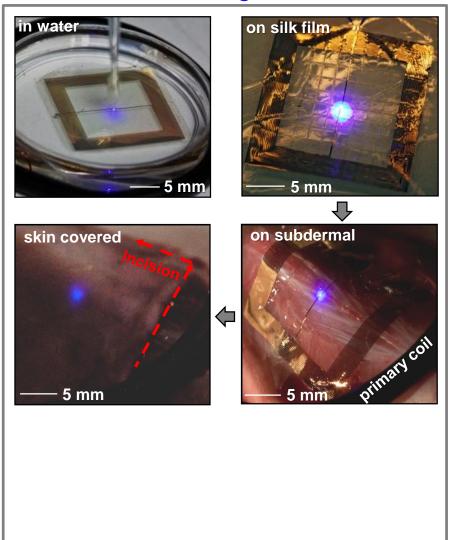
Bendable system



Multi-pixels and stretchable system



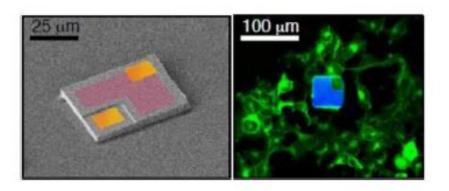
Bio-Integration

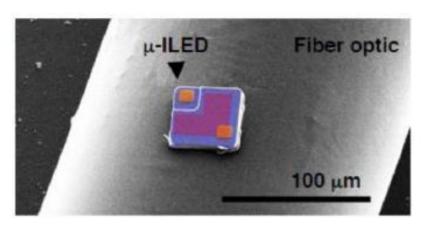




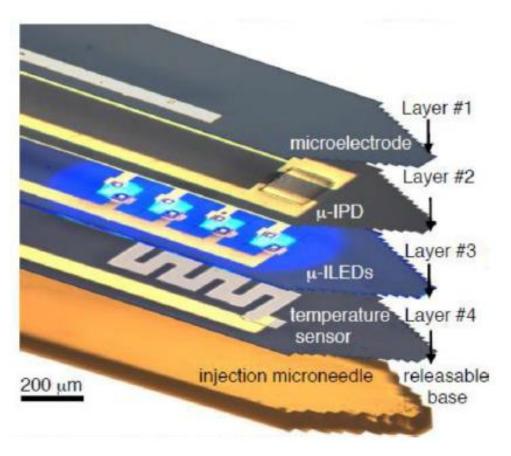
Cellular scale, tiny LEDs for implantable devices

Cellular scale LEDs





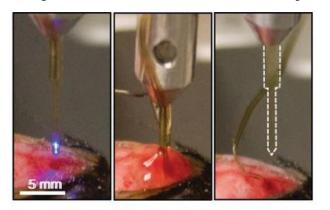
Multifunctional integrated systems

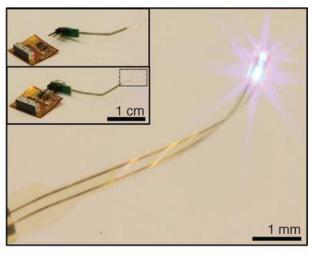


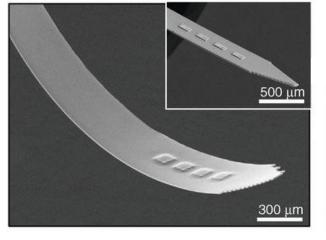


Cellular scale, tiny LEDs for implantable devices

Injectable LEDs for freely moving mice







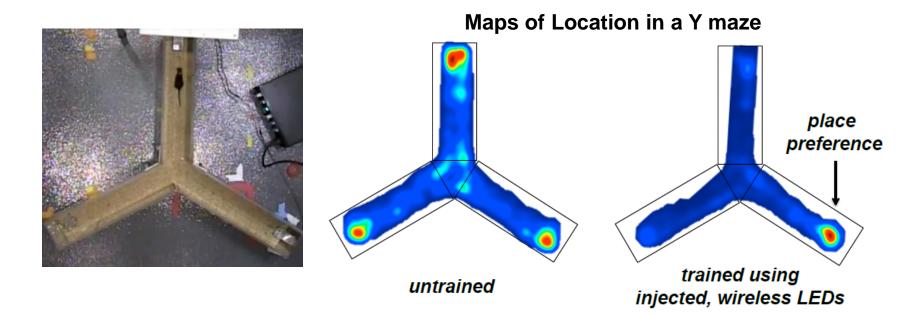


Conventional
Optogenetics
(Optical fibers)

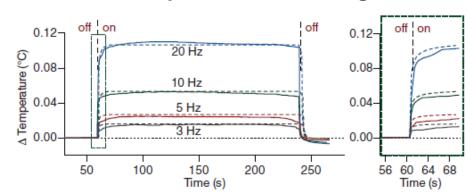




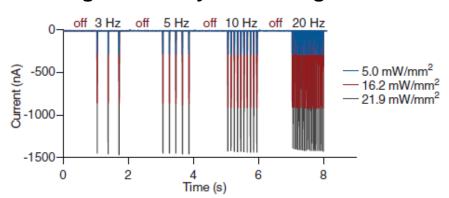
Cellular scale, tiny LEDs for implantable devices



Temperature monitoring



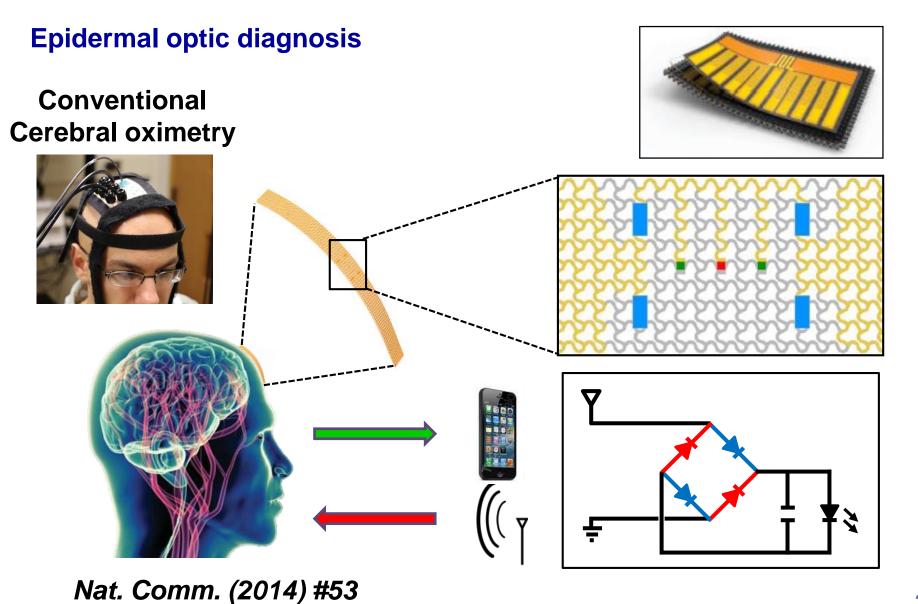
Light intensity monitoring



Science 340, 211 (2013)

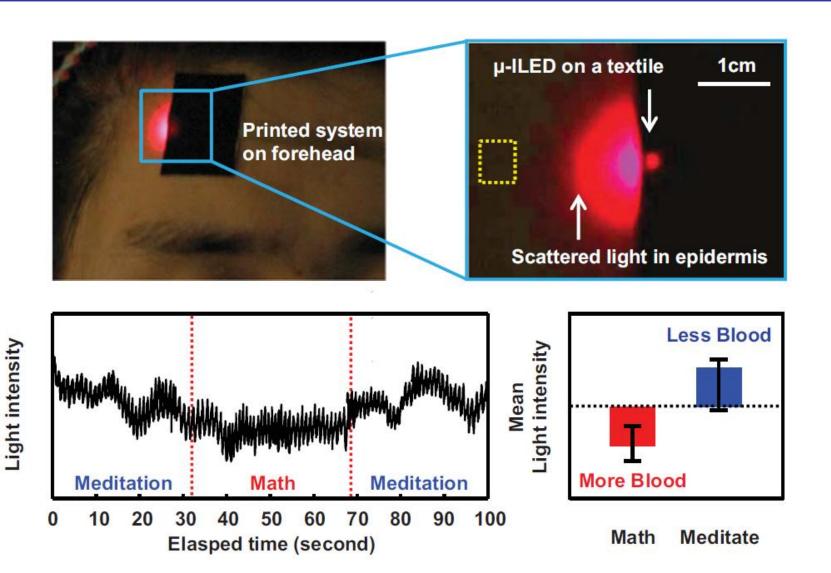


Patch-type LEDs for Cerebral Oximetry





Patch-type LEDs for Cerebral Oximetry



Nat. Comm. (2014) #53